

Abstract

A self-aligned conductive region to active region structure is disclosed in which parallel
5 active regions of a semiconductor region of a substrate, which extends to a surface, are
separated by STI regions. The STI regions have an insulator liner layer grown over their
sides and are filled with an insulator filler layer. Equally spaced gate insulator regions,
formed prior to the STI regions, are disposed over the active regions and overlap a portion of
the insulator liner layer. Conductive regions, formed prior to the STI regions, are disposed
10 over the gate insulator regions.

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